Precise studies on He-Processing and HPR for Recovery from Field Emission by using X-ray Mapping System

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### Our status of cERL Main linac cryomodule



### TUAA01 TUPB021

cERL Commissioned started in Dec. 2013. 20MeV 10uA (Dec.2013 – Jun.2014) 20MeV <u>100uA</u> (Jan.2015 – Jun.2015)

Requirement was satisfied at V.T. Heavy F.E was met. Onset is 8 MV/m after string assembly.



### Motivation of study (He process)

- For recovering from bad performance of cavities, there are several ways;
  - without disassembly: RF processing , He processing, plasma processing(?)
  - with disassembly: HPR, EP, CP
- High power pulse processing was applied to our cERL main linac cryomodule and suppressed Q-degradation now. But Q did not recovered now.
- It was reported that He processing would worked effectively (Jlab). But it might be risky for directly applying He processing in our cryomodule. And we want to know
  - what is happening on He processing? And how is it effective or risky?



First we try to understand the <u>mechanism of He processing</u> and <u>effectiveness of HPR</u> to reduce the field emission by using <u>X-ray rotating mapping system</u> in vertical tests

### Study by using KEK-ERL #2 cavity

- We fabricated the prototype of cERL main linac cavity as #2 cavity before cERL ML cryomodule assembly.
- This cavity have good performance.
- We start the field emission study in V.T by using this cavity with X-ray mapping system.

KEK-ERLmodel-2cavity #2 at V.T stand with xray mapping system



- Field emission onset is about 16MV/m.
- Quench free up to 30MV/m.



	VT	Surface treatment etc.	Aim of VT
	7th VT	(Warm-up)	System check of He processing
	8th VT	(Warm-up)	Study on He processing
	9th VT	Flange disassembly/assembly <u>(not apply HPR)</u>	Check flange disassembly/assembly procedure to simulate module assembly
	10th VT	(Warm-up)	Study on He processing (2)
	11th VT	HPR (assembly all flanges)	HPR study

Precise study of He processing (2 times) from 7<sup>th</sup> VT & HPR from  $11^{th}$  VT .

## **Rotating X-ray and T-mapping system**



Radiation profile of 9cell cavity could be obtained by using PIN diode all over 360°





## He processing trial (1)

2 emitters could be observed before He processing.

•1 emitters remained and 1 emitter disappeared after He processing.

Before He processing :10^-8Pa

•<u>Q-value recover little bit and</u> radiation on-set increased from <u>17MV/m to 19MV/m.</u>

7<sup>th</sup> V.T



### 8<sup>th</sup> V.T After He processing: 10^-8Pa



## Detail of He processing (1) (behavior during He processing)

Q0 (before and during He processing)

10<sup>10</sup>

10<sup>9</sup>

0

Q0 (7th pi 1st)

- Q0 (7th pi 4th)

15

10

**During He** 

5

 $10^{-3} \sim 10^{-4}$  Pa level of He.

processing

#### Before He processing (25MV/m 10<sup>-8</sup>Pa)





Radiation was irradiated all over cavity surface

### Results of reassembly work of (9<sup>th</sup> V.T)



Many radiation emitters were appeared even at 18MV/m

## He processing trial (10th)

- We applied "Enhance mode" of He processing.
- 4 emitters remained, other 4 emitters disappeared or decreased and new 2 emitter appeared after He processing.
- Q-value and radiation on-set did not change.

#### Before He processing 18MV/m (1.3\*10<sup>-8</sup> Pa)





#### After He processing18MV/m (8.2x10<sup>-5</sup> Pa)



## Two status of He processing

Two status appear during He processing

- Radiation all over cavities. ~All surface mode~
  - Like discharge? Plasma?
  - It occurs at vacuum level around 10<sup>^-2</sup> Pa.
- 2 Radiation are strongly activated. ~Enhanced mode~
  - Some emitters can be activated. But some can not.
  - It occurs at vacuum level of  $10^{-3} \sim 10^{-4}$  Pa.

### Pattern ①







HPR works well to remove FE sources and gain of onset was 6MV/m.

## <u>Summary</u>

#### [He processing]

- We tried He processing twice at vertical test.
  - Condition time is limited by radiation safety and He consumption.
- Two states of enhanced radiation status were observed.
  - <u>"All surface mode "</u>, which was appeared at 10<sup>-2</sup> Pa and irradiated all surface.
  - <u>"Enhanced mode"</u>, which was appeared at 10 -3<sup>~-4</sup> Pa and enhanced locally.
- At moment , our statistics are too small to make conclusion. However, it indicates;
  - "Enhanced mode" seems to be effective,
  - about half of emitter could be processed,
  - sometimes new emitter appear.  $\rightarrow$  we will correct more statistics.
  - "All surface mode" did not processed within our limited time → need more long time ?

### [HPR]

- The observed emitters were drastically removed after HPR.
- It indicates HPR is effective to remove field emission sources finally.

### Next

We will try to He processing to our cERL ML cryomodule after testing of input coupler conditioning with He line not to break the ceramic window by He processing

Input coupler He processing setup



# Acknowledge & ...

- First of all, I'd like to thank Compact ERL Grp member.
- I'd like to thank Mike Drury (Jlab) for the support and discussing about He processing.



To the memory of <u>Kenji Shinoe</u> who was decreased yesterday. He mainly worked all He line construction in these experiments

### (b) Reassembly work for jacket welding (with Ar purge 8/18)

Seal : viton , flange : SS316L flange all components were browed by ion gun so that particles remain 0 @ 0.3um. Class 10 Nitrilile ambidextrouse Glove used





Change Ar purge point to LBP, before the flange open, we change the flow 200ml/min to a few l/min not to enter the other particles from the flange





Before changing flange, we use Teflon pad not to enter other particles. This procedure is same as V.T assembly work.



Before changing flange, we blow the hole of screws by ion gun so that the particle count is 0 except for the 4 screw port.



All screws of flanges of SS316L were plated by silver and ultrasonic cleaned and browed by ion gun to particles 0

### (b) Reassembly work for jacket welding (to VT stand 8/21)

Seal : Tin coated helicoflex , flange : SS316L flange , Class 10 Nitrilile ambidextrouse Glove used . All screws of flanges of SS316L were plated by silver and ultrasonic cleaned all components were blowed by ion gun so that particles remain 0 @ 0.3um

Input port Screw hole blowd so that particle is 0 except for 4 screws.sam e procedure were done at all flanges



Tin coated Helico flex

Flange of SBP side

### LBP side



### SBP side

Before setting helicon, wiped by archol

# Summary of recovery work

- We simulate the assembly work during cryomodule assembly of Ar purge and reassembly work of flange exchanges and did the vertical test after this individual work one by one.
- First we tried only Ar purge work (pump & purge) twice. This work did not make worse the cavity performance by V.T.
- Next we simulated the reassembly work. After reassembly work, we measure the cavity performance again. Field emission was started on 10MV/m, which was lowered from before reassembly (onset 18MV/m).
- Furthermore, we measured the X-ray mapping after reassembly work. Many radiation traces were observed after reassembly.
- From these results, <u>during reassembly work, we enter some particles and/or the dust ?</u>

#### Future plan

- To investigate the particle contamination process through the string assembly, we continue V.T by applying each procedure.
- We will try the test bench in clean room in detail (particle enter , air flow survey).
- Furthermore, we also doubt the assembly work of the outside connection of GV. So we try new open clean bench.

Flow measure by fog generation in clean room (AVIS)



New clean bench Class 1 (open clean bench) KOACH (Koken camany)







## History of #2 cavity

	VT	Surface treatment etc.	Aim of VT
	1st VT	EP(100um), Annealing,EP2(20um), HPR, Baking	Performance check
	2nd VT	EP(20um), HPR, Baking	Performance check
	3rd VT	Warm-up	Check Q-value after warm-up
	4th VT	HPR (assembly input and bottom flanges)	HPR study
	5th VT	Keep with vacuum condition	Check reproducibility
	6th VT	Ar purge (No flange assembly)	Check Ar purge procedure
	7th VT	(Warm-up)	System check of He processing (0)
	8th VT	(Warm-up)	Study on He processing (1)
	9th VT	Flange disassembly/assembly	Check flange disassembly/assembly procedure
	10th VT	(Warm-up)	Study on He processing (2)
	11th VT	HPR (assembly all flanges)	HPR study

Precise study of He processing from 7<sup>th</sup> VT & HPR from 4<sup>th</sup> VT.

## Field emission pattern (KEK-ERL-model-2)

